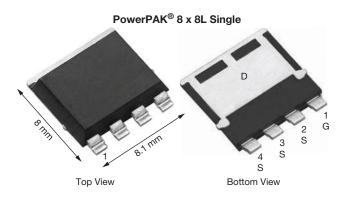
SQJQ410EL



Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	100			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0034			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.0040			
I _D (A)	135			
Configuration	Single			
Package	PowerPAK 8 x 8L			

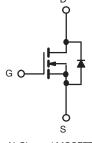


FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Fully lead (Pb)-free device
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



FREE



N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current	T _C = 25 °C	1-	135	
Continuous Drain Current	T _C = 125 °C	Ι _D	78	
Continuous Source Current (Diode Conduction)		I _S	124	А
Pulsed Drain Current ^a		I _{DM}	210	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	68	
Single Pulse Avalanche Energy	L = 0.1 IIIA	E _{AS}	231	mJ
Maximum Power Dissipation	T _C = 25 °C	D	136	W
Maximum Power Dissipation	T _C = 125 °C	P _D	45	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C
Soldering Recommendations (Peak Temperature) ^{c, d}			260	U

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^b	R _{thJA}	50	°C/W
Junction-to-Case (Drain)		R _{thJC}	1.1	0/10

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. When mounted on 1" square PCB (FR4 material).

c. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

S16-1124-Rev. A, 13-Jun-16

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SQJQ410EL

SPECIFICATIONS ($T_C = 25 \circ C$, unless othe	erwise noted)						
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static		•			•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		100	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2	2.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$= 0 \text{ V}, \text{ V}_{\text{GS}} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	-	-	500		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	50	-	-	А	
		$V_{GS} = 10 V$	I _D = 20 A	-	0.0028	0.0034		
Drain-Source On-State Resistance ^a	Р	$V_{GS} = 4.5 V$	I _D = 10 A	-	0.0033	0.0040	Ω	
Drain-Source On-State Resistance ~	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 20 A, T _J = 125 °C	-	-	0.0058		
		$V_{GS} = 10 V$	I _D = 20 A, T _J = 175 °C	-	-	0.0074		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		-	84	-	S	
Dynamic ^b								
Input Capacitance	Ciss			-	5620	7350	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	2850	3750		
Reverse Transfer Capacitance	C _{rss}			-	220	290	1	
Total Gate Charge ^c	Qg		V _{DS} = 50 V, I _D = 10 A	-	97	150		
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 V$		-	15	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	20	-		
Gate Resistance	Rg		f = 1 MHz	0.95	1.92	3	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	19	30		
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 50 \; V, \; R_{\text{L}} = 5 \; \Omega \\ I_{\text{D}} \cong 10 \; A, \; V_{\text{GEN}} = 10 \; V, \; R_{\text{g}} = 1 \; \Omega \end{array}$		-	40	60	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	69	110		
Fall Time ^c	t _f]	-	87	135	1		
Source-Drain Diode Ratings and Cha	racteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	210	А	
Forward Voltage	V _{SD}	I _F =	= 40 A, V _{GS} = 0 V	-	0.83	1.2	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

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c. Independent of operating temperature.

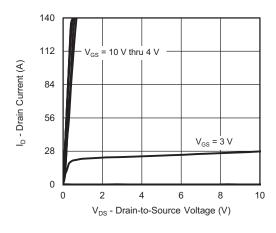
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



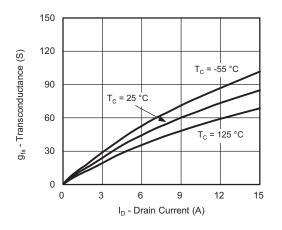
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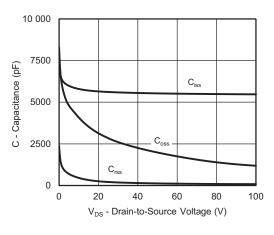
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



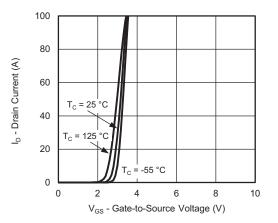
Output Characteristics



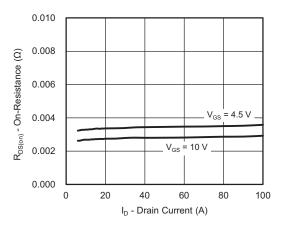
Transconductance



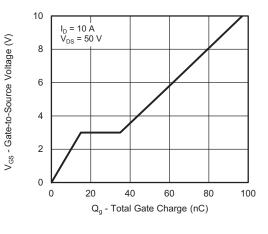
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

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3 s. contact: automostec Document Number: 76643

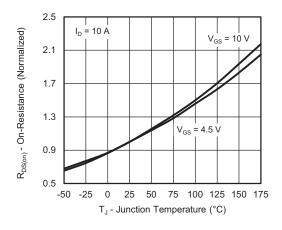
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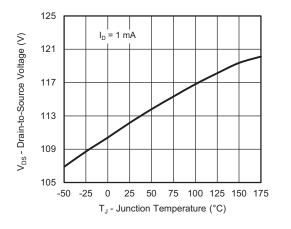
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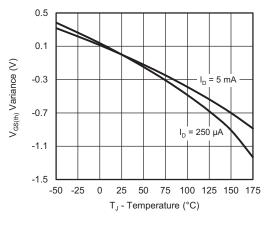
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



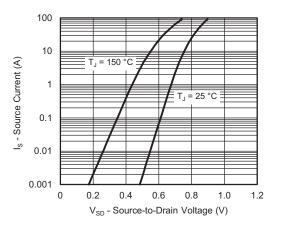
On-Resistance vs. Junction Temperature



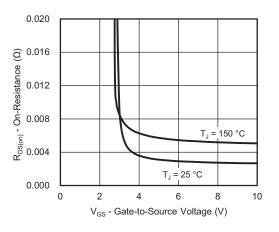
Drain Source Breakdown vs. Junction Temperature



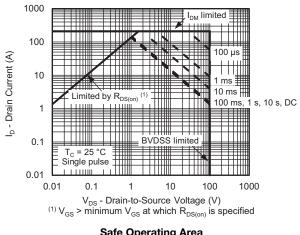
Threshold Voltage



Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Safe Operating Area

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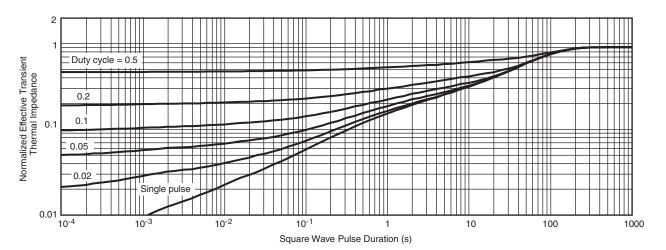
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Document Number: 76643

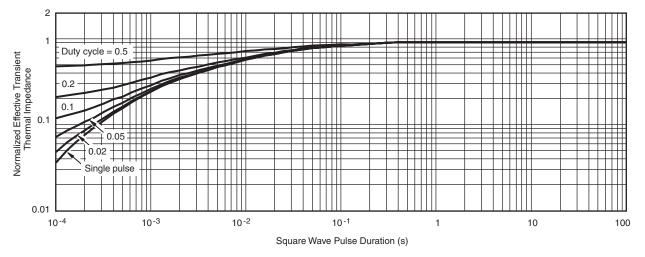
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK[®] 8 x 8L

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK 8 x 8L package:

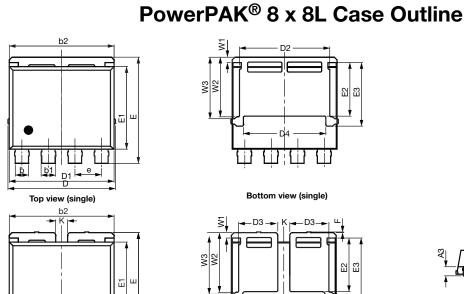
DATASHEET PART NUMBER	OLD ORDERING CODE ^a	NEW ORDERING CODE
SQJQ100EL	-	SQJQ100EL-T1_GE3
SQJQ402E	SQJQ402E-T1-GE3	SQJQ402E-T1_GE3
SQJQ410EL	-	SQJQ410EL-T1_GE3
SQJQ900E	-	SQJQ900E-T1_GE3

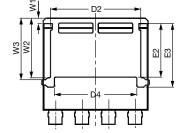
Note

a. Old ordering code is obsolete and no longer valid for new orders

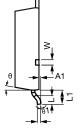
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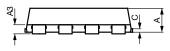




Bottom view (single)



0.25 gauge line





¥, D3 🗕 _D3 W3 W2 Ш

Bottom view (dual)

DIM.		MILLIMETERS			INCHES	
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	1.70	1.80	1.90	0.067	0.071	0.075
A1	0.00	0.08	0.13	0.000	0.003	0.005
A3	0.55	0.62	0.70	0.022	0.024	0.028
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	7.80	7.90	8.00	0.307	0.311	0.315
С	0.20	0.25	0.30	0.008	0.010	0.012
D	8.00	8.10	8.25	0.315	0.319	0.325
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D3	2.85	2.95	3.05	0.112	0.116	0.120
D4	6.11	6.21	6.31	0.241	0.244	0.248
е	1.95	2.00	2.05	0.077	0.079	0.081
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	3.94	4.04	4.14	0.140	0.159	0.163
E3	4.69	4.79	4.89	0.185	0.189	0.193
F	0.05	0.10	0.15	0.002	0.004	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
К	0.80	0.90	1.00	0.031	0.035	0.039
W	0.30	0.40	0.50	0.012	0.016	0.020
W1	0.30	0.40	0.50	0.012	0.016	0.020
W2	4.39	4.49	4.59	0.173	0.177	0.181
W3	4.54	4.64	4.74	0.179	0.183	0.187
θ	6°	10°	14°	6°	10°	14°
θ1	0°	3°	8°	0°	3°	8°
-0891-Rev. A, G: 6026	06-Oct-14					

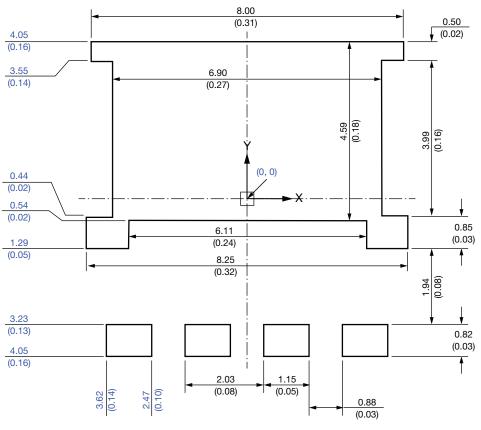
Revision: 06-Oct-14

1 For technical questions, contact: pmostechsupport@vishay.com Document Number: 67734

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Recommended Minimum PADs for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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